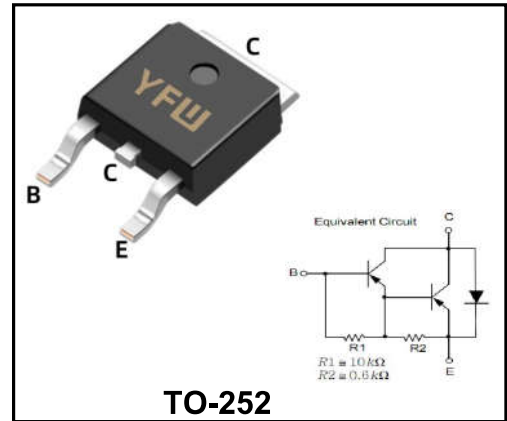


**PNP Plastic-Encapsulate Transistors
Darlington Transistor**

Medium Power Linear Switching Applications
‡Complementary to MJD112



Absolute Maximum Rating (Ta=25°C)

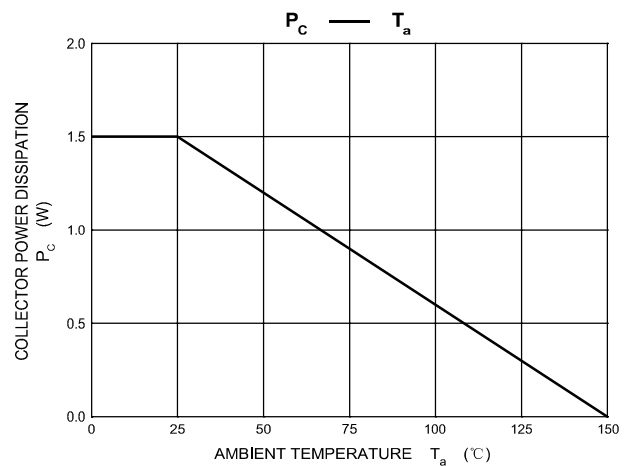
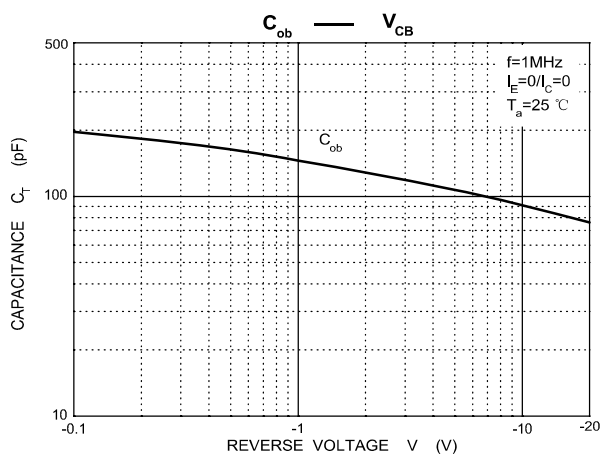
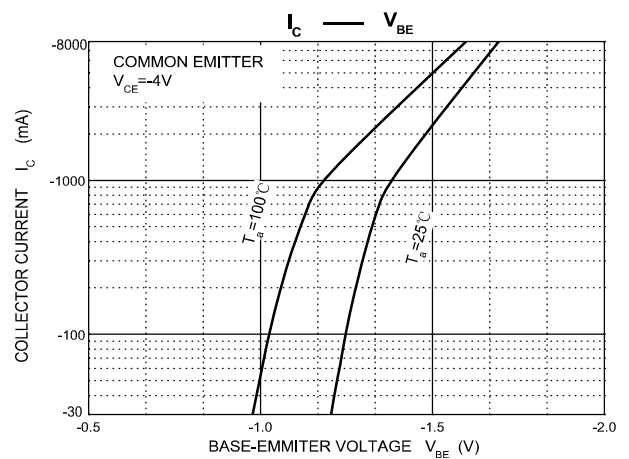
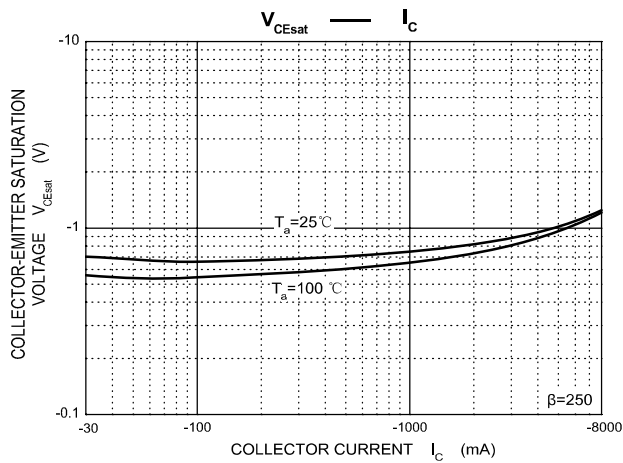
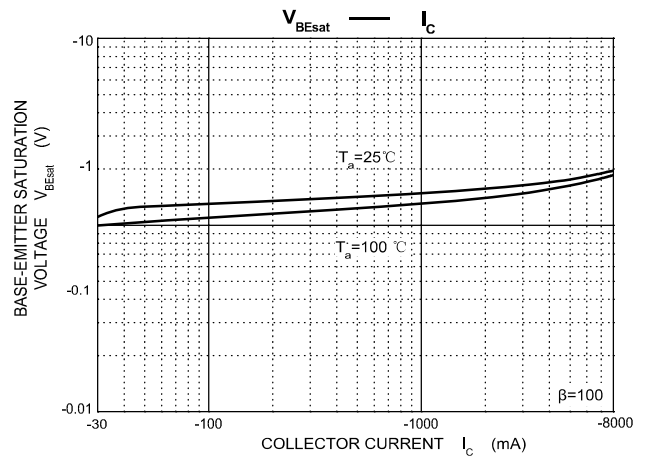
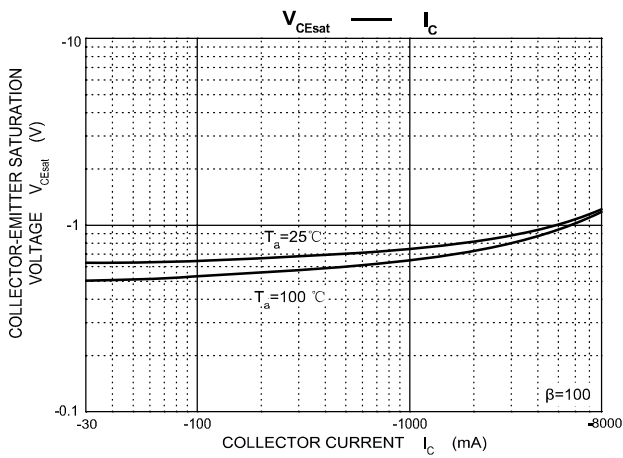
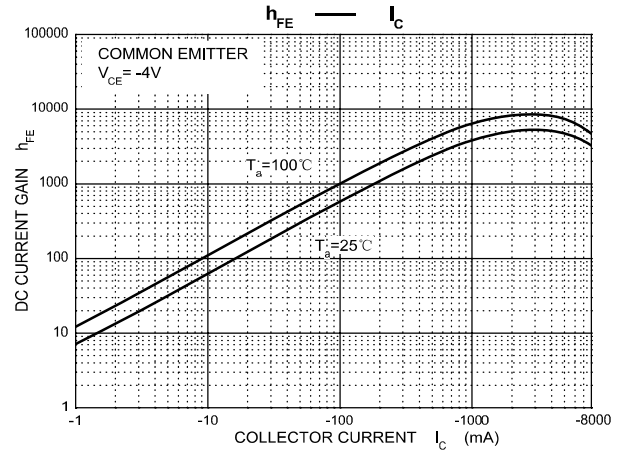
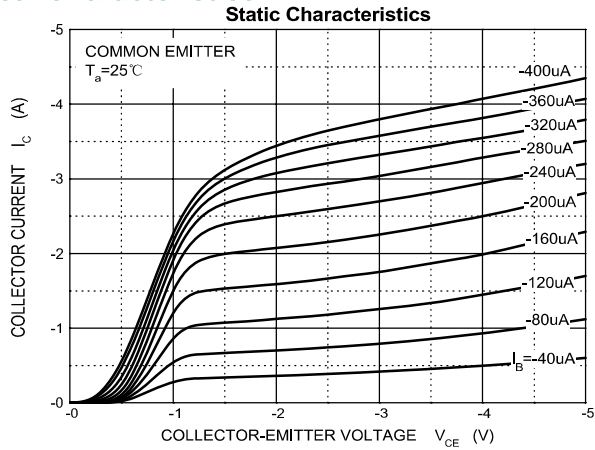
Parameter	Symbol	Value	Unit	
Collector-Base Voltage	V_{CBO}	-100	V	
Collector-Emitter Voltage	V_{CEO}	-100	V	
Emitter-Base Voltage	V_{EBO}	-5	V	
Collector Current(DC)	I_C	-3	A	
Collector Dissipation	P_C	$T_C = 25\text{ }^\circ\text{C}$	20	W
		$T_a = 25\text{ }^\circ\text{C}$	1.75	W
Junction Temperature	T_j	150	$^\circ\text{C}$	
Storage Temperature	T_{stg}	-65~150	$^\circ\text{C}$	

Electrical Characteristics (Ta=25°C)

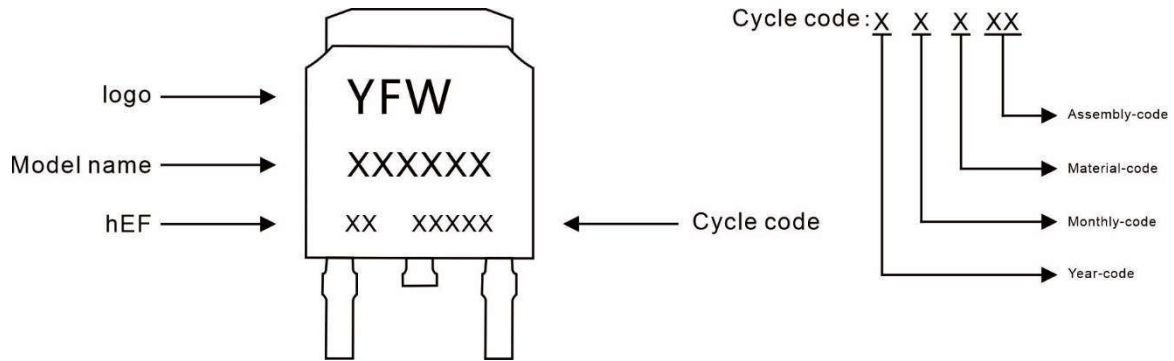
Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_C = -30\text{mA}, I_B = 0$	-100			V
Collector cut-off current	I_{CBO}	$V_{CB} = -100\text{V}, I_E = 0$			-0.2	mA
Collector cut-off current	I_{CEO}	$V_{CE} = -50\text{V}, I_E = 0$			-0.5	mA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-0.2	mA
* DC current gain	h_{FE}	$V_{CE} = -3\text{V}, I_C = -0.5\text{A}$ $V_{CE} = -3\text{V}, I_C = -3\text{A}$	1000 1000			
*Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -3\text{A}, I_B = -12\text{mA}$ $I_C = -5\text{A}, I_B = -20\text{mA}$			-2 -4	V
* Base-Emitter ON Voltage	$V_{BE(on)}$	$V_{CE} = -3\text{V}, I_C = -3\text{A}$			-2.5	V
Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 0.1\text{MHz}$			100	pF

* Pulse Test : $PW \leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

Typical Characteristics



Marking Diagram



Ordering information

Model name	Package	Unit Weight	Base Quantity	Packing Quantity
MJD127	TO-252	0.011oz(0.32g)	2500pcs/reel	5000pcs/box 25000pcs/Carton

Package Dimensions

TO-252

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.50	0.087	0.098
A1	0.00	0.12	0.000	0.005
A2	2.20	2.40	0.087	0.094
B	1.20	1.60	0.047	0.063
b	0.50	0.70	0.020	0.028
b1	0.70	0.90	0.028	0.035
c	0.40	0.60	0.016	0.024
c1	0.40	0.60	0.016	0.024
D	6.35	6.65	0.250	0.262
D1	5.20	5.40	0.205	0.213
E	5.40	5.70	0.213	0.224
e	2.20	2.40	0.087	0.094
e1	4.40	4.80	0.173	0.189
L	10.00	11.00	0.393	0.433
L1	2.70	3.10	0.106	0.122
L2	1.40	1.80	0.055	0.071
L3	0.90	1.50	0.035	0.059

Disclaimer

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